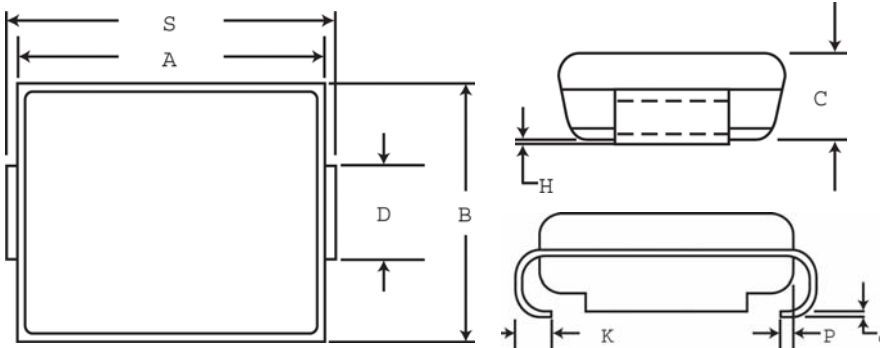
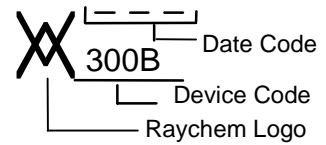


Specification Status: Released

PHYSICAL DESCRIPTION



Marking:



A		B		C		D**		H		J		K	
MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX
4.06	4.57	3.30	3.81	1.90	2.41	1.96	2.11	0.051	0.152	0.15	0.30	0.76	1.27
(0.160)	(0.180)	(0.130)	(0.150)	(0.075)	(0.095)	(0.077)	(0.083)	(0.002)	(0.006)	(0.006)	(0.012)	(0.030)	(0.050)

P	S	
	MIN	MAX
REF	0.51	5.59
	(0.020)	(0.220)

*Rounded off approximation
** D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P

Other Physical Characteristics

Form Factor: SMB (Surface Mount, JEDEC DO-214AA Package)
Lead Material: Matte Tin finish
Encapsulation Material: Epoxy, meets UL94 V-0 requirements
Solderability: per MIL-STD-750, Method 2026
Solder Heat Withstand: per MIL-STD-750, Method 2031
Solvent Resistance: per MIL-STD-750, Method 1022
Mechanical Shock: per MIL-STD-750, Method 2016
Vibration: per MIL-STD-750, Method 2056

Tape and Reel packaging per EIA 481-1

Agency Recognition: UL
Precedence: This specification takes precedence over documents referenced herein.
CAUTION: Operation beyond the rated voltage or current may result in rupture, electrical arcing or flame.

Materials Information

RoHS Compliant ELV Compliant

Directive 2002/95/EC
Compliant

Directive 2000/53/EC
Compliant

OBSOLETE
NOT the LATEST
REVISION

SiBar™ Thyristor Surge Protectors

Raychem Circuit Protection Products

PRODUCT: TVB300SB-L

DOCUMENT: SCD 25603
PCN: E05012
REV LETTER: C
REV DATE: APRIL 28, 2007
PAGE NO.: 2 OF 2

DEVICE RATINGS @ 25° C (Both Polarities)

Parameter	Symbol	Value	Units
Repetitive Off-State Voltage, Maximum at ID = 5 μA	VDM	300	V
Non-Repetitive Peak Impulse Current	IPP ₁	80	A
Telcordia GR-1089 CORE 10x1000 μs	IPP ₂	100	A
TIA-968 lightning Type A Metallic 10/560 μs	IPP ₃	150	A
Double exponential Waveform	IPP ₄	250	A
TIA-968 lightning Type A Longit. 10/160 μs	IPP ₅	250	A
Telcordia GR-1089 Intrabuilding 2/10 μs	IPP ₆	100	A
(Notes 1 and 2)	IPP ₇	100	A
IEC61000-4-5 (Voc 1.2/50us) 8/20 μs			
ITU-T K.20/K.21 (Voc 10/700us) 5/310 μs			
TIA-968 lightning Type B (Voc 9/720us) 5/320 μs			
Critical Rate of Rise of On-State Current	di/dt	500	A/μs
Powered Pulse Amplifier, C=30μF, V=600V	di/dt	170	A/μs
Maximum 2x10 μsec waveform, V _{OC} =1.25kV, I _{SC} =250A peak			

DEVICE THERMAL RATINGS

Parameter	Symbol	Value	Units
Storage Temperature Range	TSTG	-55 to 150	°C
Operating Temperature Range Blocking or conducting state	TA	-40 to 125	°C
Overload Junction Temperature Maximum; Conducting state only	TJ	+150	°C
Maximum Lead Temperature for Soldering Purpose; for 10 seconds	TL	+260	°C

ELECTRICAL CHARACTERISTICS Both polarities (T_J @ 25°C unless otherwise noted)

Characteristics	Symbol	Min	Typ	Max	Units
Breakover Voltage (+25°C) (dv/dt = 0.4kV/μs, I _{sc} =900mA, V _{dc} = 500V (both polarities))	VBO	----	350	400	V
Breakover Voltage Temperature Coefficient	dVBO/dTJ	----	0.1	-----	%/°C
Off-State Current (VD1=50V)	ID1	----	-----	2.0	μA
(VD2=VDM)	ID2=IDM	----	-----	5.0	μA
On-State Voltage (IT=1A)	VT	----	-----	4.0	V
(PW ≤ 300 μsec, Duty Cycle ≤ 2% (Note 2))					
Breakover Current	IBO	----	-----	800	mA
Holding Current (Note 2)	IH	150	-----	----	mA
Peak Onstage Surge Current (Measured @ 60Hz, 1 cycle, 600V)	ITSM	30			A
Critical Rate of Rise of Off-State Voltage (Linear waveform, V _D = 0.8 X Rated V _{BO} , T _J = +25°C)	dv/dt	2000	----	----	V/μs
Capacitance (f=1.0 Mhz, 50V _{DC} bias, 1Vrms)	C1	----	21	----	pF
(f=1.0 Mhz, 2V _{DC} bias, 1Vrms)	C2	----	42	----	pF

Note 1. Allow cooling before testing second polarity

Note 2. Measured under pulse conditions to reduce heating

VOLTAGE-CURRENT CHARACTERISTIC

